EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"US 20090066345"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2010/06/07 09:42
S2	3	"3978508".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 09:44
S3	2	"20080006844".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 10:37
S4	873205	(force or pressure or position or finger$2print) near10 sens$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 12:33
S5	3880	(organic near10 field near10 effect near10 transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 12:34
S6	41621	(organic near10 field near10 effect near10 transistor) or (organic near5 semiconduct$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 12:35
S7	1543	S4 and S6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 12:35
S9	962244	((glass or ceramic or plastic or polymer or polymer or metal or metal or paper) near30 substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 12:37

S10	2399	((pentacene or thiophene or oligothiophene or polythiophene or fluorene) near30 (active or channel))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 12:38
S11	27	S4 and S6 and S9 and S10	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 12:38
S12	2	"20090066345".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 12:45
S13	2	"20030071259".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 12:46
S14	1	S4 and S6 and S9 and S10 and "20030071259".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 12:50
S15	3135	(organic near5 field near5 effect near5 transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 17:09
S17	873205	(force or pressure or position or finger$2print) near10 sens$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 17:10
S18	123	S15 and S17	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 17:10
S19	2	"20020105080".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 17:53

S20	1553	(substrate near15 diaphragm) and (measure $5 near15 diaphragm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 17:58
S21	1161	(substrate near15 diaphragm) and (measure $5 near15 diaphragm) and ((pressure or position or force) near15 sens$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:00
S22	1	(substrate near15 diaphragm) and (measure $5 near15 diaphragm) and ((pressure or position or force) near15 sens$5) and (organic near15 transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:01
S23	1	(substrate near15 diaphragm) and (measure $5 near15 (deformation or bend$4)) and ((pressure or position or force) near15 sens$5) and (organic near15 transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:04
S24	4729	(organic near10 field near10 effect near10 transistor) or (otft)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:09
S25	968856	(force or position or pressure or fingerprint) near30 sens$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:11
S26	11979	(diaphragm or diaphram) near30 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:11
S27	1	S24 and S25 and S26	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:11
S28	1610987	(force or position or pressure or fingerprint) near30 (sens$4 or detect $4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:12

S29	4665	S25 and S26 and S28	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:12
S30	1	S24 and S25 and S26 and S29	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:13
S31	1	S24 and S25 and S26 and S29	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:13
S32	67	((HAGEN) near2 (KLAUK)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/07 18:14
S33	76	((MARCUS) near2 (HALIK)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/07 18:14
S34	38	((UTE) near2 (ZSCHIESCHANG)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/07 18:14
S35	45	((GUENTER) near2 (SCHMID)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/07 18:14
S36	1	((GRZEGORZ) near2 (DARLINSKI)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/07 18:15
S37	7	((RAINER) near2 (WASER)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/07 18:15
S38	40	((RALF) near2 (BREDERLOW)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/06/07 18:15
S39	1	S32 and S33 and S34 and S35 and S36 and S37 and S38	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:16
S40	2	(qimoda near2 ag).asn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:18
S41	2	"4827085".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:24

S42	1701385	(force or position or pressure) near30 (sen$4 or detect$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:28
S43	97	(force or position or pressure) near30 (sen$4 or detect$4) near30 (regular near15 array)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:28
S44	28727	(driv$4 and measur$4) near30 (drain or source)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:36
S45	1	S43 and S44	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:36
S46	3	"3795898".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/07 18:46
S47	3465	(measur$5 near30 source near30 drain near30 gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 11:01
S48	159	(measur$5 near30 source near30 drain near30 gate) and ((pressure or position or force) near30 sens$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 11:02
S49	31	(measur$5 near30 source near30 drain near30 gate) and ((pressure or position or force) near30 sens$4) and (constant near30 gate near30 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 11:05
S50	12	(sens$4 near30 measur$5 near30 source near30 drain near30 gate) and ((pressure or position or force) near30 sens$4) and (constant near30 gate near30 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 11:10

S51	6459	((force or pressure) near30 (change near30 (voltage or current)) near30 (detect$5 or sens$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 11:49
S52	6425	((force or pressure) near30 change near30 (voltage or current) near30 (detect$5 or sens$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 11:50
S53	6425	(force or pressure) near30 change near30 (voltage or current) near30 (detect$5 or sens$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 11:50
S54	262	(sensing or detecting) near30 measur$5 near30 (source and drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 13:36
S55	2	"20030218194".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 13:41
S56	1	"20030218194".did. and (sensing or detecting) near30 measur$5 near30 (source and drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 13:41
S57	44	(sensing or detecting) near30 measur$5 near30 (source and drain) and (force)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 13:47
S58	8667	(diaphragm near30 (detecting or sensing) near30 (force or pressure))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 14:35
S59	1	(diaphragm near30 (detecting or sensing) near30 (force or pressure) near30 (source near5 drain))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 14:36

S60	33	diaphragm near30 (force or pressure) near30 (source near5 drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 14:58
S61	19543	(pressure or force) near30 diaphragm near30 sens$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 15:19
S62	1874	(pressure or force) near30 (diaphragm near30 substrate) near30 sens$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 15:19
S63	187	(pressure or force) near30 (diaphragm near30 substrate) near30 sens$4 and (transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 15:19
S64	2	(pressure or force) near30 (diaphragm near30 substrate) near30 sens$4 near30 (source and drain) and (transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 15:36
S65	1768	(array near30 force near30 sens$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 15:55
S66	275	(array near30 force near30 sens$4) and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 15:55
S67	2	"20050248335".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 15:59
S69	2	"4827085".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 16:01

S70	158	row near30 address near30 decoder near30 gate near30 terminal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 16:29
S71	10	row near30 address near30 decoder near30 gate near30 terminal near30 driving	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 16:29
S72	2	"20060138599".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 16:54
S73	4	((finger near5 print) near30 sens$4) and (perfluorinated)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 16:56
S74	755	((force or pressure) near30 sens$4) and (perfluorinated)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 17:00
S76	5	(protective near30 layer) and otft and (perfluorinated)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 17:02
S77	40	otft and (perfluorinated)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 17:02
S78	147	((organic near10 thin near10 film near10 transistor) or otft) and (perfluorinated)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/08 17:03
S79	2	"5543944".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/09 08:18

S80	4290	(hydrophilic near30 hydrophobic) near30 (passivation or encapsulat $4 or protect$4 or dielectric or insulat$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/09 08:24
S81	355	(hydrophilic near30 hydrophobic) near30 (passivation or encapsulat $4 or protect$4 or dielectric or insulat$3) and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/09 08:24
S87	1	"20040253375".did. and ("156" near30 "144")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/09 08:49

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